

STARPOWER

SEMICONDUCTOR

IGBT

GD100HFU120C2S

1200V/100A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra switching speed as well as short circuit ruggedness. They are designed for the applications such as electronic welder and inductive heating.

Features

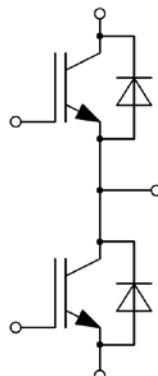
- NPT IGBT technology
- 10 μ s short circuit capability
- Low switching losses
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Switching mode power supply
- Inductive heating
- Electronic welder

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	140	A
	@ $T_C=80^{\circ}\text{C}$	100	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	200	A
P_D	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	694	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.90	3.35	V	
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		3.60			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.0	6.1	7.0	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			2.5		Ω	
C_{ies}	Input Capacitance			6.60		nF	
C_{res}	Reverse Transfer Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.51		nF	
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		1.08		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=5.6\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		300		ns	
t_r	Rise Time			64		ns	
$t_{d(off)}$	Turn-Off Delay Time			340		ns	
t_f	Fall Time			105		ns	
E_{on}	Turn-On Switching Loss				6.76		mJ
E_{off}	Turn-Off Switching Loss				4.25		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=5.6\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		320		ns	
t_r	Rise Time			65		ns	
$t_{d(off)}$	Turn-Off Delay Time			350		ns	
t_f	Fall Time			13		ns	
E_{on}	Turn-On Switching Loss				10.2		mJ
E_{off}	Turn-Off Switching Loss				5.50		mJ
I_{sc}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		900		A	

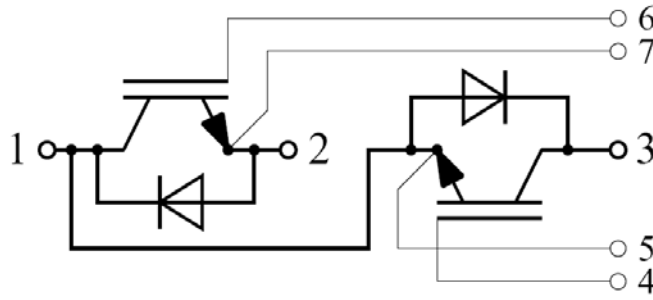
Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.95	2.40	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.85		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1900\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		5.4		μC
I_{RM}	Peak Reverse Recovery Current			11.2		A
E_{rec}	Reverse Recovery Energy			81		mJ
Q_r	Recovered Charge			101		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1900\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		3.54		A
E_{rec}	Reverse Recovery Energy			6.57		mJ

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

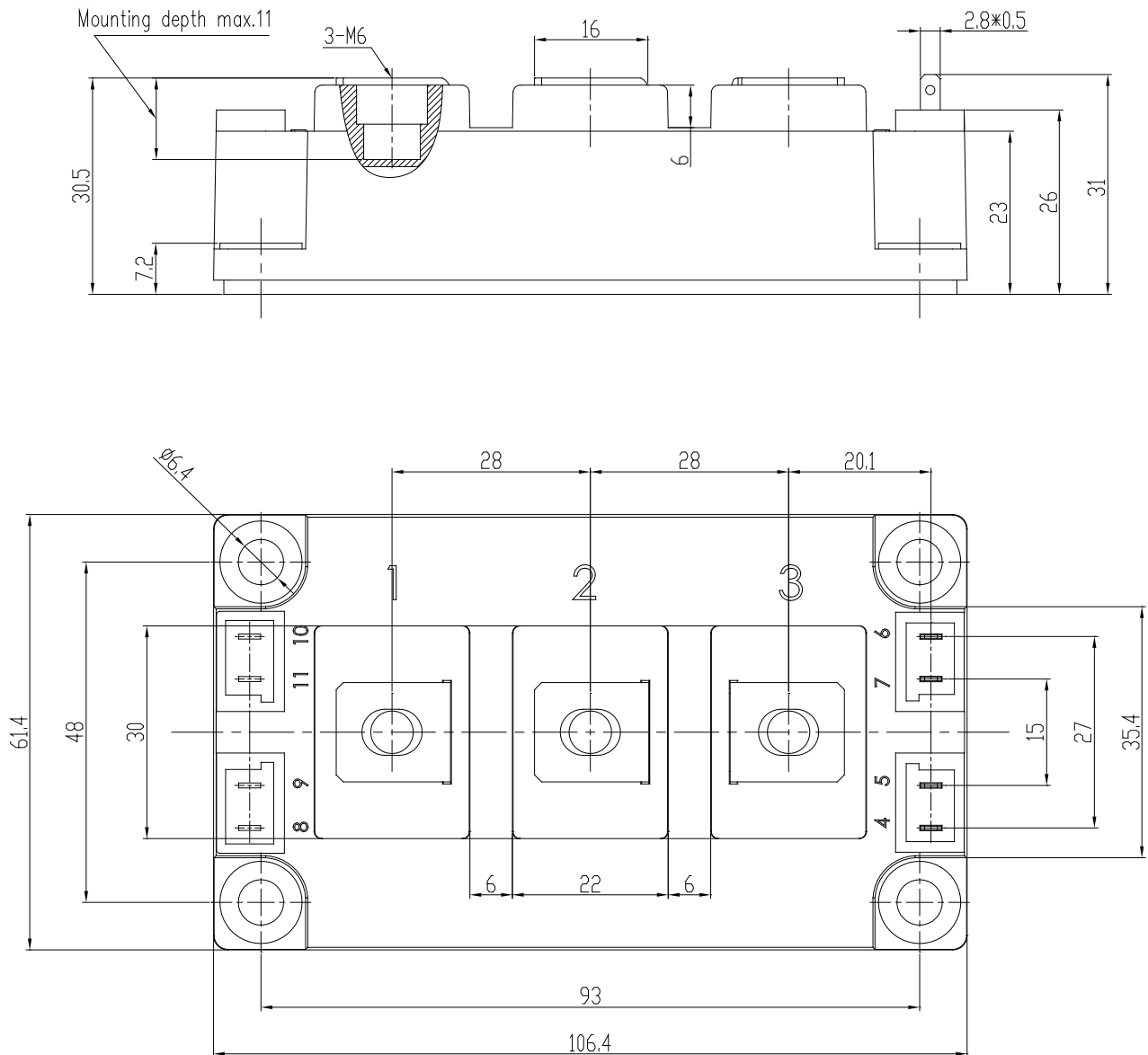
Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			30	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.180	K/W
	Junction-to-Case (per Diode)			0.377	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.103		K/W
	Case-to-Heatsink (per Diode)		0.217		
	Case-to-Heatsink (per Module)		0.035		
M	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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